

Leistungsstarke IR-Lumineszenzdiode
High Power Infrared Emitter
Lead (Pb) Free Product - RoHS Compliant

SFH 4203



Wesentliche Merkmale

- Leistungsstarke GaAs-LED (35 mW)
- Hoher Wirkungsgrad bei kleinen Strömen
- Homogene Abstrahlung
- Typische Peakwellenlänge 950 nm

Features

- High Power GaAs-LED (35 mW)
- High Efficiency at low currents
- Homogeneous Radiation Pattern
- Typical peak wavelength 950 nm

Anwendungen

- Industrieelektronik
- „Messen/Steuern/Regeln“
- Automobiltechnik
- Sensorik
- Alarm- und Sicherungssysteme
- IR-Freiraumübertragung

Applications

- Industrial electronics
- For drive and control circuits
- Automotive technology
- Sensor technology
- Alarm and safety equipment
- IR free air transmission

Typ Type	Bestellnummer Ordering Code	Strahlstärkegruppierung ¹⁾ ($I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$) Radiant Intensity Grouping ¹⁾ $I_e \text{ (mW/sr)}$
SFH 4203	Q65110A2499	8 (> 4)

¹⁾ gemessen bei einem Raumwinkel $\Omega = 0.01 \text{ sr}$ / measured at a solid angle of $\Omega = 0.01 \text{ sr}$

Grenzwerte ($T_A = 25\text{ °C}$)**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	3	V
Durchlassstrom Forward current	I_F (DC)	100	mA
Stoßstrom, $t_p = 10\text{ }\mu\text{s}$, $D = 0$ Surge current	I_{FSM}	1	A
Verlustleistung Power dissipation	P_{tot}	180	mW
Wärmewiderstand Sperrschicht - Umgebung bei Montage auf FR4 Platine, Padgröße je 16 mm ² Thermal resistance junction - ambient mounted on PC-board (FR4), pads size 16 mm ² each	R_{thJA}	450	K/W
Wärmewiderstand Sperrschicht - Lötstelle bei Montage auf Metall-Block Thermal resistance junction - soldering point, mounted on metal block	R_{thJS}	200	K/W

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	λ_{peak}	950	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	$\Delta\lambda$	40	nm
Abstrahlwinkel Half angle	φ	± 65	Grad deg.
Aktive Chipfläche Active chip area	A	0.09	mm ²
Abmessungen der aktiven Chipfläche Dimensions of the active chip area	$L \times B$ $L \times W$	0.3×0.3	mm

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics** (cont'd)

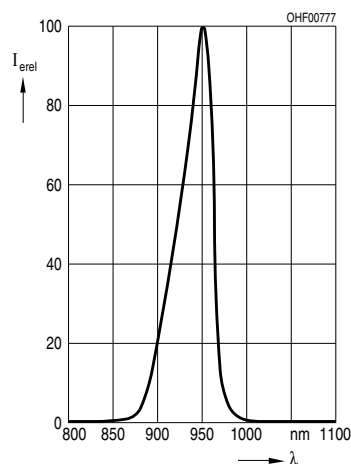
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$, $R_L = 50\text{ }\Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$, $R_L = 50\text{ }\Omega$	t_r , t_f	10	ns
Durchlassspannung Forward voltage $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	V_F V_F	1.5 (≤ 1.8) 3.2 (≤ 4.3)	V V
Sperrstrom Reverse current $V_R = 3\text{ V}$	I_R	0.01 (≤ 10)	μA
Gesamtstrahlungsfluss Total radiant flux $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	Φ_e	35	mW
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100\text{ mA}$	TC_I	- 0.44	%/K
Temperaturkoeffizient von V_F , $I_F = 100\text{ mA}$ Temperature coefficient of V_F , $I_F = 100\text{ mA}$	TC_V	- 1.5	mV/K
Temperaturkoeffizient von λ , $I_F = 100\text{ mA}$ Temperature coefficient of λ , $I_F = 100\text{ mA}$	TC_λ	+ 0.2	nm/K

Strahlstärke I_e in Achsrichtunggemessen bei einem Raumwinkel $\Omega = 0.01\text{ sr}$ **Radiant Intensity I_e in Axial Direction**at a solid angle of $\Omega = 0.01\text{ sr}$

Bezeichnung Parameter	Symbol	Werte Values	Einheit Unit
Strahlstärke Radiant intensity $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	$I_{e\text{ min.}}$ $I_{e\text{ typ.}}$	4 8	mW/sr mW/sr
Strahlstärke Radiant intensity $I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	$I_{e\text{ typ.}}$	48	mW/sr

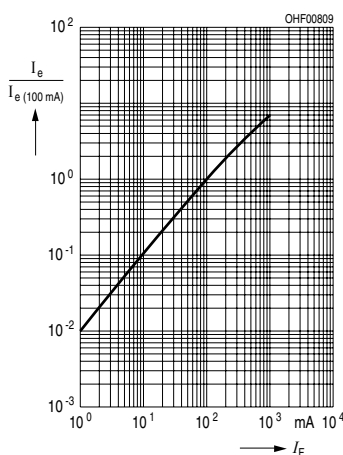
Relative Spectral Emission

$$I_{\text{rel}} = f(\lambda)$$



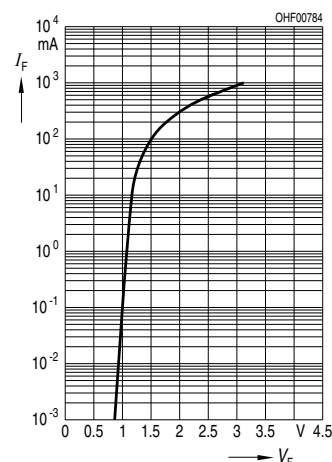
$$\text{Radiant Intensity } \frac{I_e}{I_e \text{ 100 mA}} = f(I_F),$$

single pulse, $t_p = 20 \mu\text{s}$

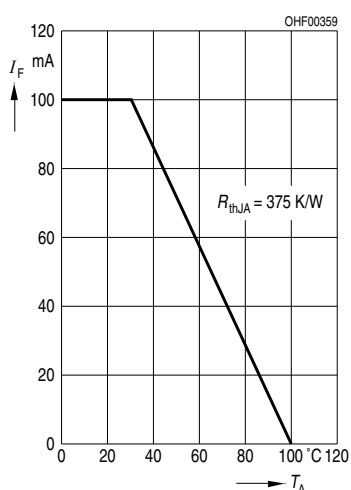


$$\text{Forward Current } I_F = f(V_F),$$

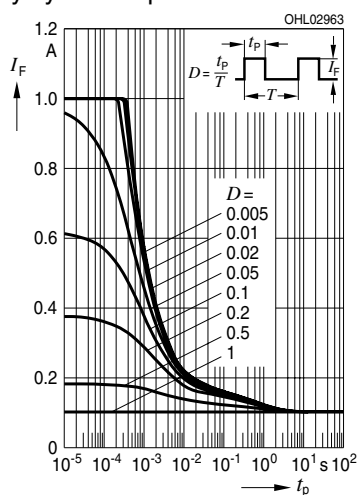
single pulse, $t_p = 20 \mu\text{s}$

**Max. Permissible Forward Current**

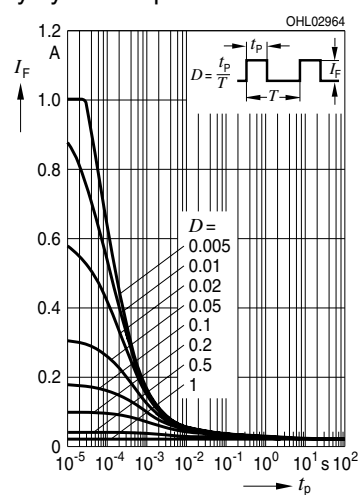
$$I_F = f(T_A, R_{\text{thJA}}^1)$$

**Permissible Pulse Handling Capability**

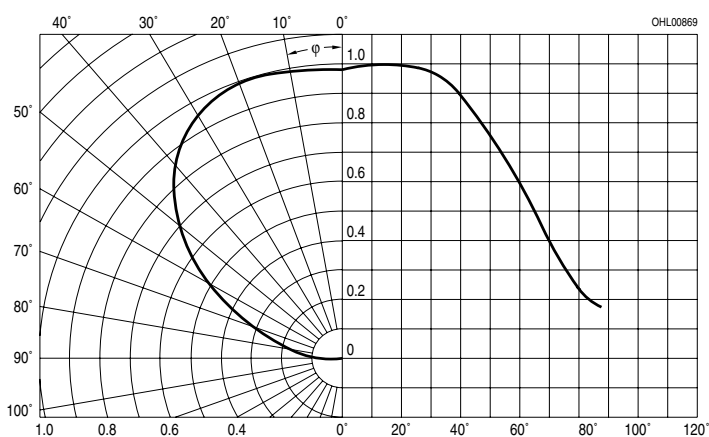
$$I_F = f(t_p, T_A = 25^\circ\text{C}, \text{Duty cycle } D = \text{parameter})$$

**Permissible Pulse Handling Capability**

$$I_F = f(t_p, T_A = 85^\circ\text{C}, \text{Duty cycle } D = \text{parameter})$$

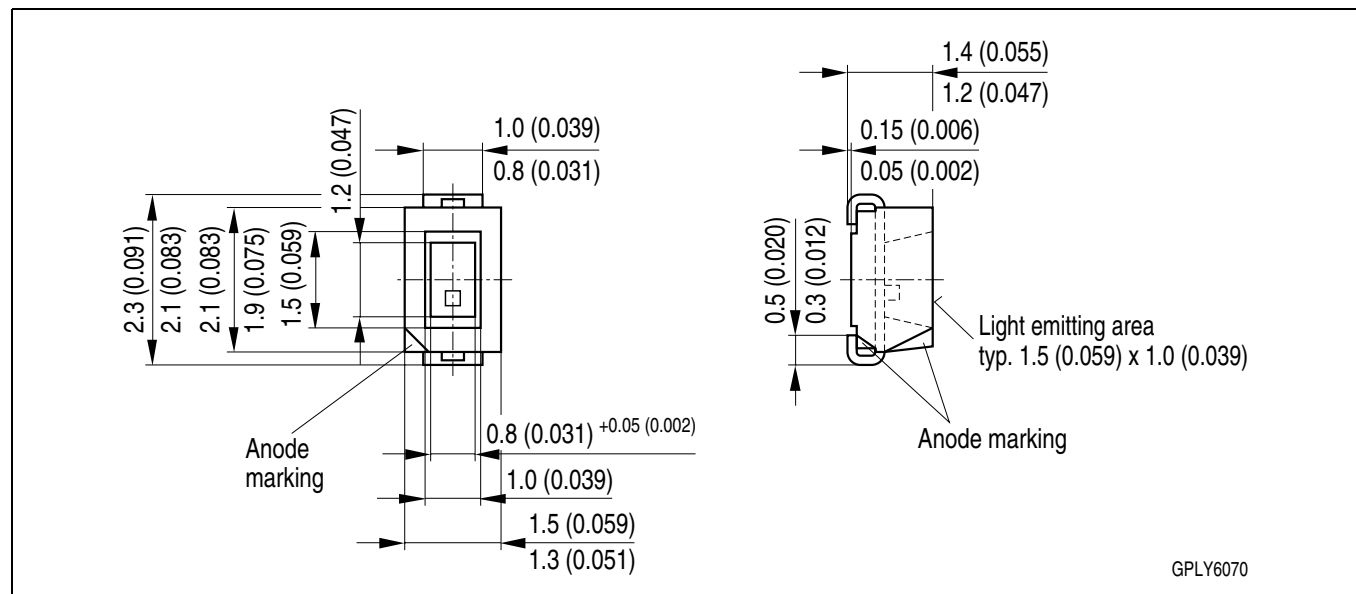
**Radiation Characteristics**

$$I_{\text{rel}} = f(\varphi)$$



¹⁾ Thermal resistance junction - ambient mounted on PC-board (FR4), pad size 16 mm² (each).

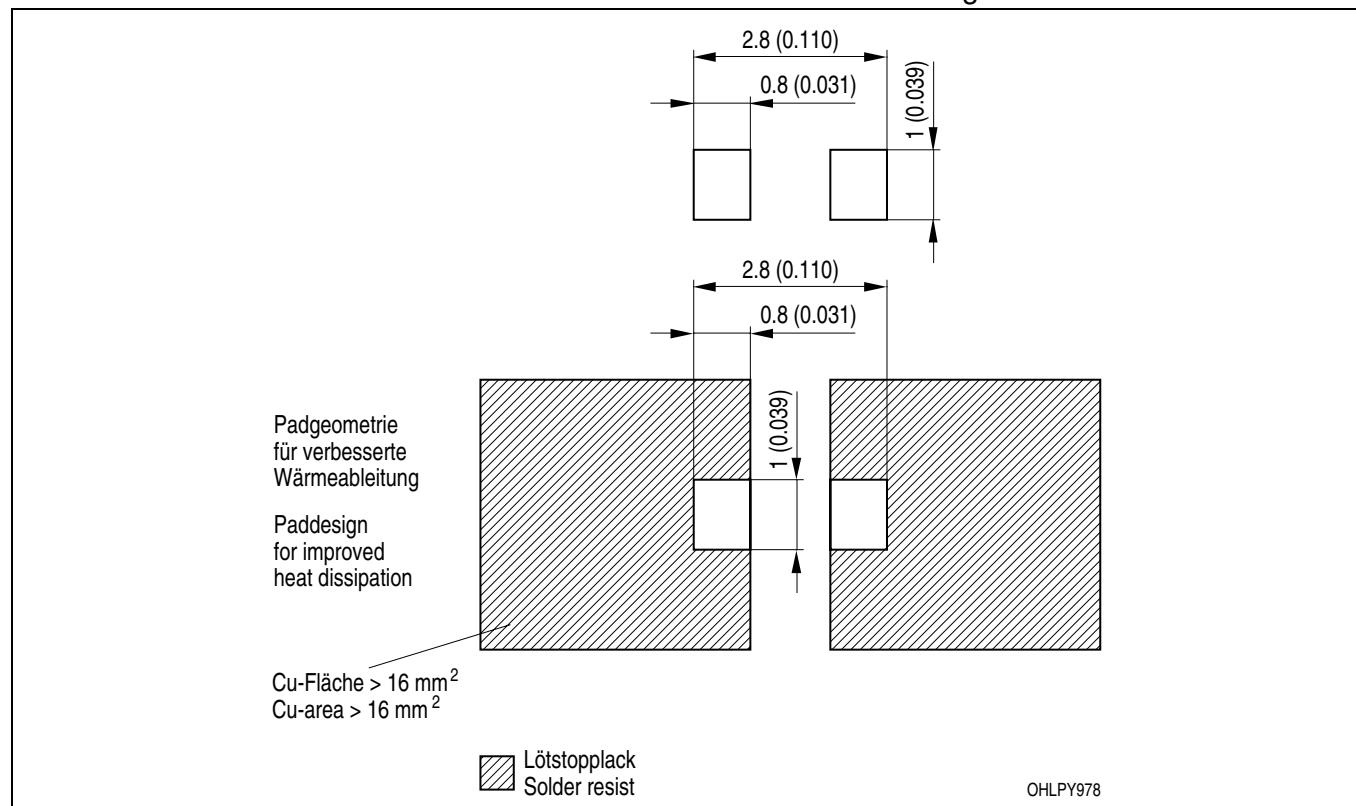
Maßzeichnung Package Outlines



Maße in mm (inch) / Dimensions in mm (inch).

Empfohlenes Lötpaddesign Recommended Solder Pad

Reflow Löten Reflow Soldering



Maße in mm (inch) / Dimensions in mm (inch).

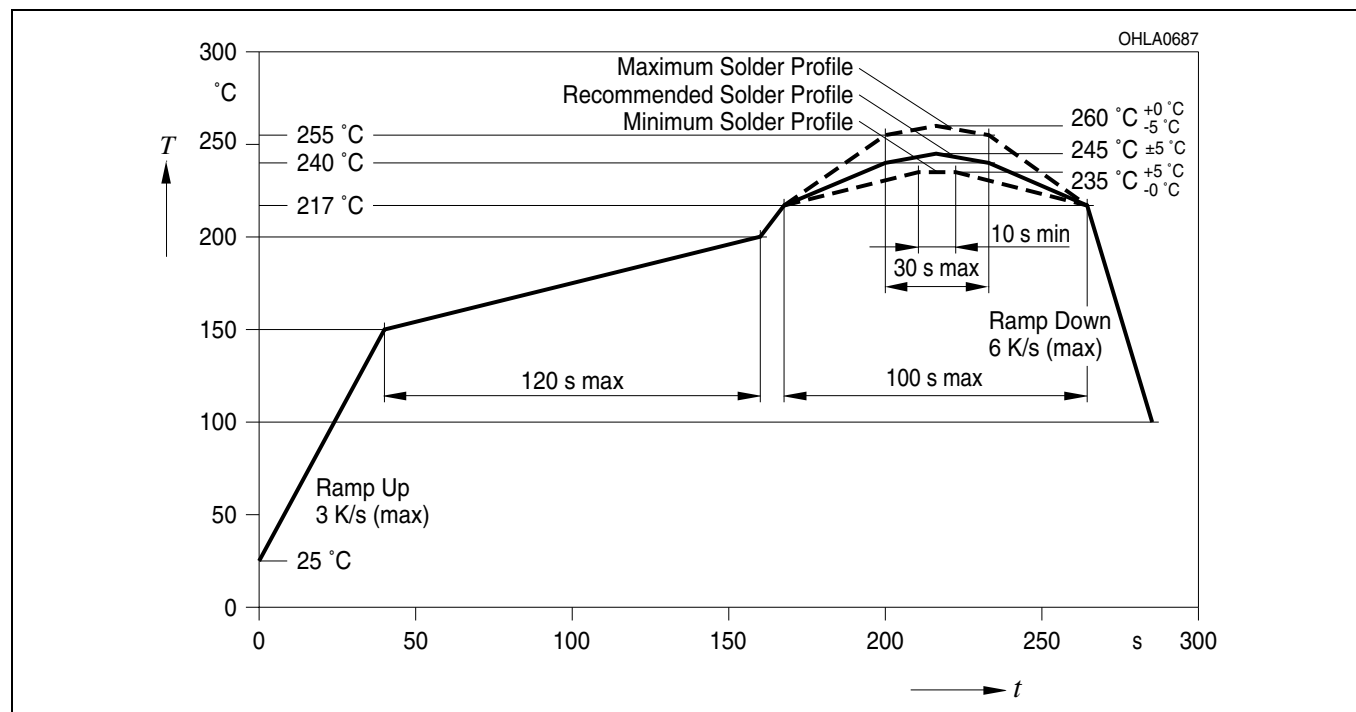
Lötbedingungen**Soldering Conditions****Reflow Lötprofil für bleifreies Löten****Reflow Soldering Profile for lead free soldering**

Vorbehandlung nach JEDEC Level 2

Preconditioning acc. to JEDEC Level 2

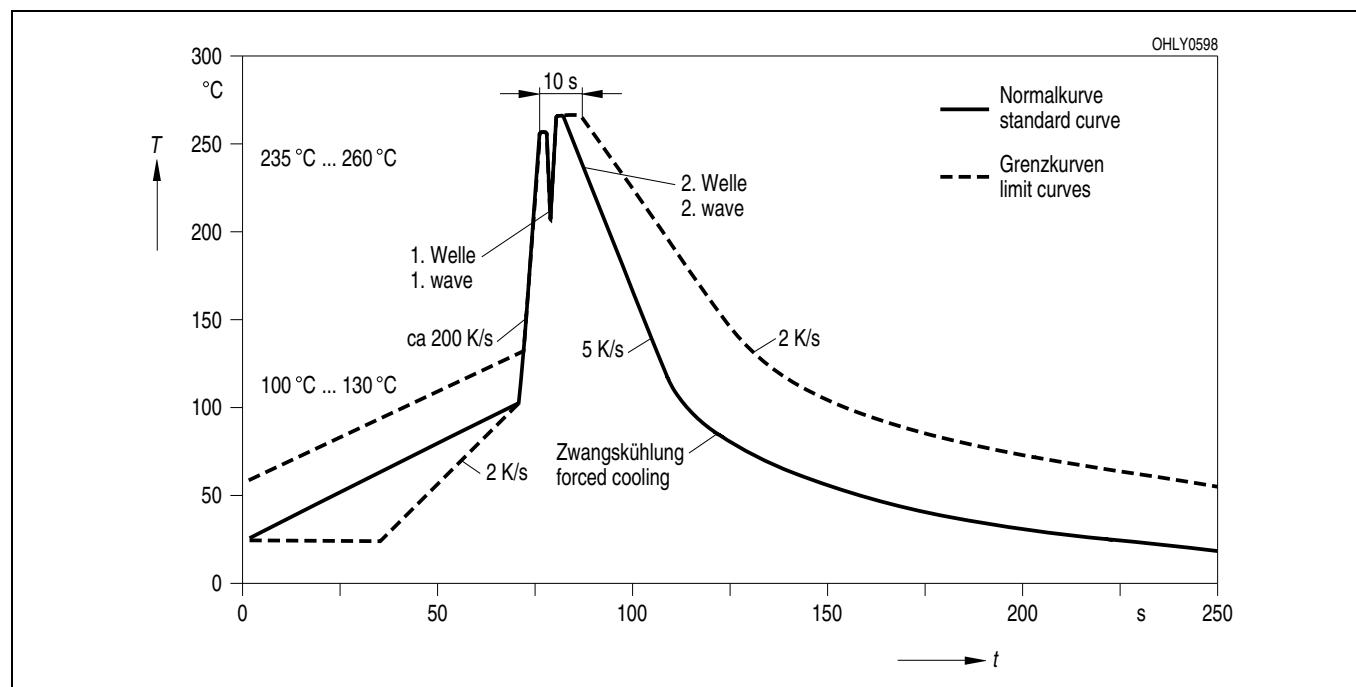
(nach J-STD-020C)

(acc. to J-STD-020C)

**Wellenlöten (TTW)****TTW Soldering**

(nach CECC 00802)

(acc. to CECC 00802)



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¹ A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

² Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.

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